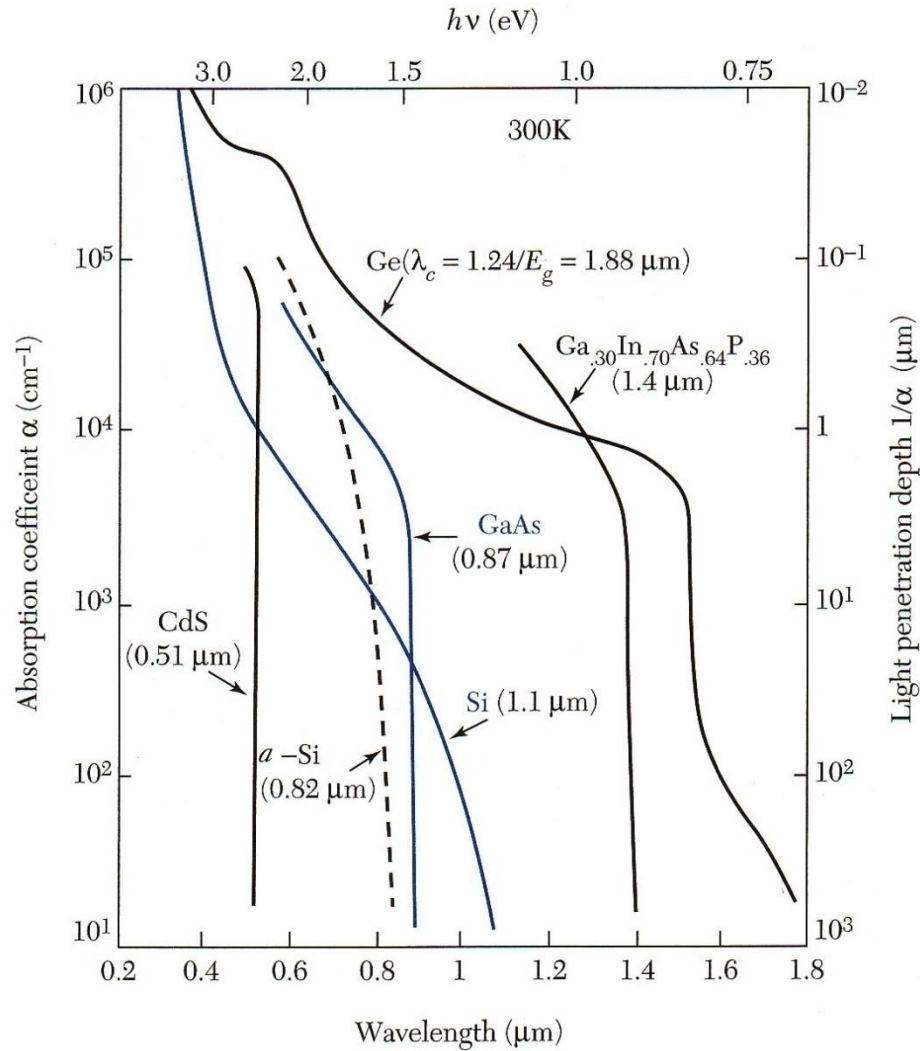


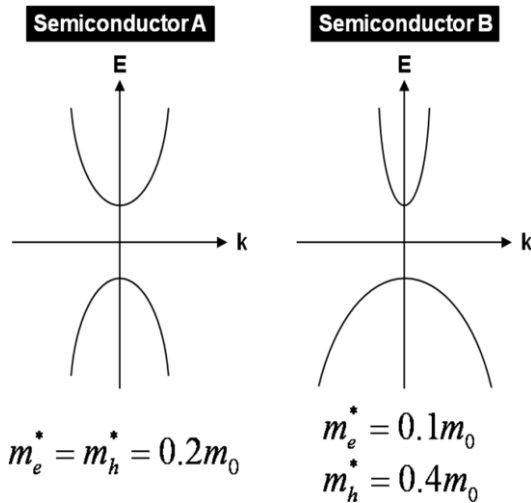
HW #2

Due September 20 (Thursday) in class

- Calculate the absorption coefficient of GaAs at 300 K as a function of the photon energy, from 1 to 2 eV, using material parameters listed in Appendix K of Chuang's textbook (pp. 708-711). For the hole effective mass, use that of the heavy hole. Assume effective mass approximation (parabolic E-k relation). Superimpose your plot on the data shown below, and observe how well they match. (Digitize the absorption curve below so you can include them in your plotting program).



- Consider two semiconductors with the following energy band diagrams: Both semiconductors have the same bandgap energy (1 eV) and the same optical matrix elements.
 - Which semiconductor has larger absorption coefficient for a photon energy of 1.1 eV? What is the ratio of their absorption coefficients?
 - Which semiconductor has wider separation of quasi-Fermi levels when the electron and hole concentrations are both $N = P = 5 \times 10^{18}$ cm⁻³?



3. Refer to the diagram below. Under biased condition, both conduction and valence bands are populated. The electron distribution in conduction band is described by Fermi-Dirac distribution, $f_C(E_2)$, with quasi-Fermi energy F_C . The electron distribution in valence band is described by Fermi-Dirac distribution, $f_V(E_1)$, with quasi-Fermi energy F_V . Here, E_1 and E_2 are related by an optical transition (i.e., they have the same k).
 - a. Use the energy reference below (i.e, $E_V = 0$ and $E_C = E_g$, the bandgap energy), find E_1 and E_2 as functions of the photon energy, $\hbar\omega$.
 - b. Derive $f_C(E_2(\hbar\omega))$ as a function of $\hbar\omega$.
 - c. Derive $f_V(E_1(\hbar\omega))$ as a function of $\hbar\omega$.
 - d. Assuming $E_g = 1$ eV, $F_C - F_V = 1.2$ eV, $m_e^* = 0.1m_0$, $m_h^* = 0.4m_0$. Calculate and plot the emission probability $f_e(\hbar\omega) = f_C(E_2(\hbar\omega)) \cdot 1 - f_V(E_1(\hbar\omega))$ for photon energies from 0.8 to 1.5 eV. Plot for two temperatures: $T = 0$ and $T = 300$ K.
 - e. Repeat part d) for the Fermi inversion factor: $f_g(\hbar\omega) = f_C(E_2(\hbar\omega)) - f_V(E_1(\hbar\omega))$

